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Determination of proton related damage on commercial and high-ohmic silicon pad diodes

P. Allport¹, N. Attree¹, F. Bowen¹, J. Cowper¹, L. Gonella¹, P. Knights¹, I. Kopsalis¹, J. Matthews¹, <u>K. Nikolopoulos¹</u>, B. Phoenix¹, T. Price¹,

¹University of Birmingham







Medical Cyclotron at the University of Birmingham

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Comparison between facilities



- Radiation hardness critical for HL-LHC detectors and beyond
- World-wide campaigns to characterise radiation hardness of sensors and components
- Within AIDA-2020, transnational access to 10 European Facilities was supported
 - CERN maintains a database with 158 irradiation facilities worldwide
 - https://irradiation-facilities.web.cern.ch/



NIEL and the Hardness factor



- For comparison: fluences expressed in equivalent 1 MeV neutron fluence
 - Conversion via hardness factor
 - Usually derived from leakage current in the bulk of a silicon sensor
- Assumption: leakage current scales with the non-ionizing energy loss (NIEL)
 In practice, variety of approaches to estimate hardness factors:
 - MC40: κ=2.2 for 23 MeV protons [K. Nikolopoulos, IPRD2016]
 - KIT: κ= 2.05 ± 0.61 for 24 MeV protons (1.85 previously) [A. Dierlamm, RD50 Workshop in Barcelona, 2010]
 - RD50 tables: κ≅2.56 for 25 MeV protons [https://rd50.web.cern.ch/rd50/NIEL/default.html]
 - ▶ IRRAD: **κ=0.62 for 23 GeV protons** [NIM B186 (2002) 100]
- K. Nikolopoulos /RD50 Workshop, 3 June 2020/ Determination of proton related damage



Hardness factor standardisation

P. Allport,^a F. Bögelspacher,^c K. Bruce,^a R. Canavan,^a A. Dierlamm,^c L. Gonella,^a
P. Knights,^a I. Mateu,^b M. Moll,^b K. Nikolopoulos,^a B. Phoenix,^a T. Price,^a L. Ram,^a
F. Ravotti,^b C. Simpson-Allsop,^a and C. Wood^a

Experimental Determination of Proton Hardness Factors

^aUniversity of Birmingham,

Birmingham, B15 2TT, United Kingdom

at Several Irradiation Facilities

^bIRRAD Proton Facility,

CERN, CH-1211 Geneva 23, Switzerland

^c Institute of Experimental Particle Physics, Karlsruhe Institute of Technology, Karlsruhe, D-76131, Germany

E-mail: k.nikolopoulos@bham.ac.uk

ABSTRACT: The scheduled High Luminosity upgrade of the CERN Large Hadron Collider presents new challenges in terms of radiation hardness. As a consequence, campaigns to qualify the radiation hardness of detector sensors and components are undertaken worldwide. The effects of irradiation with beams of different particle species and energy, aiming to assess displacement damage in semiconductor devices, are communicated in terms of the equivalent 1 MeV neutron fluence, using the hardness factor for the conversion. In this work, the hardness factors for protons at three different kinetic energies have been measured by analysing the I–V and C–V characteristics of reverse biased diodes, pre- and post-irradiation. The sensors were irradiated at the MC40 Cyclotron of the University of Birmingham, the cyclotron at the Karlsruhe Institute of Technology, and the IRRAD proton facility at CERN, with the respective measured proton hardness factors being: 2.1 ± 0.5 for 24 MeV, 2.2 ± 0.4 for 23 MeV, and 0.62 ± 0.04 for 23 GeV. The hardness factors currently used in these three facilities are in agreement with the presented measurements.

Clear need for uniformly derived hardness factors

- Collaboration between
- University of Birmingham
- CERN

JINST 14 (2019) P12004

arXiv:1908.03049

- Karlsruhe Institute of Technology
- Measuring and comparing hardness factors with consistent methodology



Karlsruher Institut für Technologie





Silicon sensor: BPW34F

- BPW34F diode was chosen for this study
- silicon p-i-n photodiode with daylight blocking filter
- produced by OSRAM Opto-Semiconductors
- commercially available
- extensively studied

For comparison, measurements at CERN also performed with Float Zone pad diodes

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BPW34 Commercial *p-i-n* Diodes for High-Level 1-MeV Neutron Equivalent Fluence Monitoring



Fig. 3. BPW34F characteristics in reverse bias normalized to 20°C. Leakage current measurement and increasing irradiation levels with 23 GeV protons.

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Hardness factors

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Overview of results



- Common methodology applied to derive consistent set of hardness factors
 - Significant uncertainties still exist: dosimetry and measurement precision
- University of Bonn has now commissioned a proton irradiation facility [P. Wolf, 35th RD50 workshop]
- BPW34F diodes irradiated at Bonn were sent to Birmingham for measurements/comparisons
 - Work to resume once laboratory become accessible again
- K. Nikolopoulos /RD50 Workshop, 3 June 2020/ Determination of proton related damage



Set-up for precision electrical measurements



New PCB with spring loaded connection
 On-line humidity/temperature monitoring
 pA range current measurement precision
 Keithley electrometers 6517B & 6487
 Capacitance/Resistance measurements:
 Wayne Kerr 6500B series LCR meter





Hamamatsu 8x8mm² diode

(ATLAS17 strip sensor campaign)





Pad diode measurements

Test structure: pad diode with guard rings (gr)

- ▶ fabricated on p-type wafers (FZ320) by Hamamatsu for ATLAS ITk
- ▶ Nominal thickness 320 µm
- Measurements: I-V and C-V for guard ring grounded/floating/connected





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I-V measurements



For pad and guard-ring connected to different ammeters, a channel is observed between pad and guard-ring for all the investigated diodes due to missing p-stop isolation



C-V for different biasing schemes



Doping density N_D determination for pad-gr grounded biasing scheme

▶ 1/C² method: N_D = 2/($\epsilon_0 \epsilon_{Si} q_0 b$) with 1/C² = b(V+V₀); V0 ≅ V_{bi} (built-in voltage)

▶N_D=4.6·10¹² cm⁻³, V₀= 7.71 V, χ²/ndof=56.7/68

Estimate with full depletion method in next slide



Determination of Vdep

- Determination of full depletion voltage V_{dep}
- pad-only and pad-gr grounded biasing schemes
- ▶ fits for V= 80-218 V and V= 320-478 V
- Intercept of 1/C² fits below and above the full depletion
- ▶ Pad-only V_{dep} = 265.1V
- ▶ Pad+gr V_{dep} = 268.4V
- $N_D = (2\epsilon_0\epsilon_{Si}/q_0d^2)V_{dep}$

Thickness [µm]	N _D [cm⁻³] (1/C²)	N _D [cm⁻³] (V _{dep})
320	4.6 10 ¹²	3.45 10 ¹²
310	4.6 10 ¹²	3.67 10 ¹²

- Depletion depth $w(V) = \frac{\epsilon_0 \epsilon_{Si}}{C(V)}$ $V > V_{dep} \rightarrow$ active thickness for diode
- For effective active thickness need to account for edge capacitance contributions

Smartscope thickness measured consistent with 320µm K. Nikolopoulos /RD50 Workshop, 3 June 2020/ Determination of proton related damage



Estimating the planar and edge capacitance



Estimating the planar and edge capacitance

The model describes well all three biasing schemes

For "pad only" after 60V the data are described better by the pad + gr grounded area



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MC40 cyclotron University of Birmingham

Provides: p, d, ³He, and ⁴He ~continuous beams
Second beam-line into specially shielded area (2013)
▶ high dose-rate damage studies iversity of Proton current: up to 2µA
Beam spot: ~10×10 mm²
Flux: up to 10¹³ protons/s/cm²
Typical beam parameters:

- ▶ Energy: 27 MeV
- ▶ Current: 0.1-0.5µA







lon	Energy at Extraction	
Proton	11 – 38 MeV (N=1)	
	3–9 MeV (N=2)	
Deuteron	5.5 – 19 MeV (N=2)	
³ He	35 – 53 MeV (N=1)	
	9–27 MeV (N=2)	
⁴ He	11 – 37 MeV (N=2)	

Electrical measurements post-irradiation

Standard annealing procedure (80min at 60°C)

Temperature -20°C and humidity <5% RH control during measurements (nitrogen flow)</p>







I-V post irradiation and annealing



Diodes irradiated at the cyclotron in proton fluences 0.8, 1, 5.7, 8, 16 and 51 ×10¹⁴ p/cm²



Current related damage factor

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Dosimetry



Investigation of low energy component

Full beam line Geant4 simulation implemented to understand beam composition at sample

- Previous results/investigations indicated presence of low energy component in the beam
 - Led to inclusion of an upstream 350µm-thick AI plate
- Simulations suggest low energy electron component generated by proton interactions in air
 Addition of 350µm-thick AI plate upstream absorbs electrons before reaching sensor





Investigation of low energy component

Having added the AI plate other sources of low-energy electrons may become relevant Given short range, airgap between sensor and kapton critical



Ionisation chamber for beam monitoring

- Ionisation Chamber current saturates for large currents
 - general (volume) recombination (air-filled)
 - ▶ due to space charge effects (argon-filled)
- For the beam currents used the distance between the plates of an Ionisation Chamber would need to be impractically small
- Bonn uses a Secondary Electron Monitor (SEM) with very promising results
 - discussions on-going for further collaboration on improving hardness factor measurements





Summary

- Collaborative effort to standardise hardness factor measurements [JINST 14 (2019) P12004]
 - Birmingham, KIT and CERN using commercial BPW34F diodes
 - Comparisons with irradiations in Bonn on-going
 - BPW34F has several limitations when high precision is required
- High resistivity Hamamatsu diodes 8x8 mm² (ATLAS strip sensor campaign) investigated
 - Updated set-up for precision electrical measurements at Birmingham
 - I-V and C-V properties study before/after irradiation
 - Lack of p-stop isolation complicates calculation of active volume
 - Effect more pronounced following irradiation
 - Model developed to estimate the effective depletion depth
 - ▶ From estimated C_{planar} = 33.9 pF/cm² after depletion, active thickness 310±5µm determined
 - Diodes with p-stop isolation useful to control active volume
- Dosimetry largest uncertainty in hardness factor determination
 - Particle fluxes are too high for Ionisation Chambers
 - Use different foils for isotope activity: Pt foils promising
 - The Secondary Electron Monitor used by Bonn seems promising



Additional Slides



MC40 cyclotron University of Birmingham

- Provides: ³He and ⁴He acontinuous beams Second beam-line into specially shielded area (2013) high dose-rate damage studies Proton current: up to 2µA Beam spot: ~10×10 mm² Flux: up to 10¹³ protons/s/cm² Typical beam parameters:
 - Energy: 27 MeV
 - Current: 0.1-0.5µA

lon	Energy at Extraction	
Proton	11 – 38 MeV (N=1)	
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 10^{15} 1MeV-n_{eq} cm⁻² in 80s at 1µA Fluence strip sensors need to withstand at HL-LHC (3000 fb⁻¹)





Irradiation set-up

- Samples placed in temperature controlled box
 - Liquid nitrogen evaporative cooling typically -25°C during irradiation
 - Dry N₂ flow in box, typical RH~10% during irradiation
 - Temperature/humidity logged
- Feed-through for external read-out/monitoring
- Diodes mounted on Al-plate suspended from box lid
- Ni-foils front of sample for fluence measurement
- Box mounted on XY-axis robotic scanning system
 - Typical horizontal scan speed 4 mm/s



Gafchromic film used before irradiation to obtain beam position/profile



Beam energy on sample





ZAG at KIT

- The Irradiation Center Karlsruhe accesses a compact cyclotron operated by ZAG Zyklotron AG
- Proton energy at extraction: 25.3 MeV
- ▶ Typical proton current: 1.5 µA
- Temperature in box: -30°C
- Beam spot: ~ 7 mm (varying)
- ▶ Flux: ~ 2.5 × 10¹³ p/(s·cm²)
- Insulated box, cooled by cold nitrogen gas
 - Goose-necks lead gas to individual samples
 - Graphite plate to stop protons at the back
 - Window with two Kapton foils for insulation
- Samples glued on Kapton tape fixed to Al-frames
- Frames fixed in the box
- Mounted on movable XY-stage
- Horizontal speed at nominal current 115 mm/s
- Dosimetry using Nickel foils









Beam energy on sample





CERN IRRAD

- CERN Irradiation facility provided with protons from the Proton Synchrotron
- Beam momentum: 24 GeV/c
- Beam dimensions standard size: ~12x12 mm² (FWHM)
- ▶ spot size from ~6x6 mm² to ~20x20 mm² (FWHM)
- Beam intensity: ~5×10¹¹ protons/spill on cycles of 30-37 s
 - ▶ Typically: 3 spills per CPS
- ~0.7-1 x 10¹⁴ p cm⁻² h⁻¹ (on 5x5 mm² sample)





CERN IRRAD Zones

- Samples are placed in temperature controlled box
 - possible temperature down to -20°C
 - for this study irradiations at room temperature
- Box mounted on remotely controlled stage
 - sample alignment
 - beam scanning
 - Dosimetry using aluminium foil
 - Reactions: ²⁷Al(p,3pn)²⁴Na and ²⁷Al(p,3p3n)²²Na
 - Fluence measurements obtained with accuracy of ±7%





Measurement setup: Depletion Voltage



Measurements performed in aluminium box

- small fan for air circulation
- Capacitance readings at 10 kHz
- Wayne-Kerr 6500B Precision Impedance Analyser
- junction box and four coaxial cables
- Keithley 2410 Source meter for external bias
- Post-Irradiation all diodes thermally annealed
- ▶ 80 mins at 60°C





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Measurement setup: Leakage Current



- Leakage current measurements at full depletion voltage
 Using the aluminium box
- Keithley 2410 Source meter provides reverse bias
- All temperature measurements expressed at 21°C
 - Temperature during measurements stable

$$I(T_R) = I(T) \left(\frac{T_R}{T}\right)^2 e^{-\frac{E_a}{2k_B} \left[\frac{1}{T_R} - \frac{1}{T}\right]} \qquad E_a = 1.21 \text{ eV}_{\text{JINST (2013)P10003}}$$













²²Na





²⁴Na





Dosimetry



